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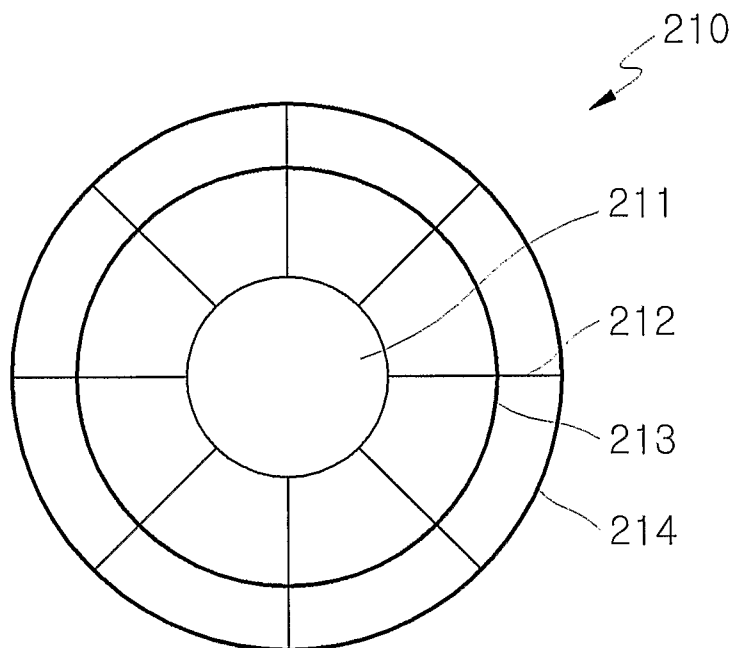
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(54) Title: PLASMA SOURCE FOR UNIFORM PLASMA DISTRIBUTION IN PLASMA CHAMBER



(57) Abstract: Disclosed herein is a plasma source which can create plasma within a reaction chamber to process a semiconductor wafer. The plasma source comprises a bushing equipped at an upper center of the reaction chamber, and a plurality of source coils linearly extending from the bushing to a periphery of the reaction chamber. With the linear source coils, it is possible to prevent deviation in magnetic field from the center to the periphery of the plasma source in the radial direction, resulting in easy control of critical dimensions and uniform etching rate both at the center and periphery of the reaction chamber.